

## isc Silicon NPN Power Transistor

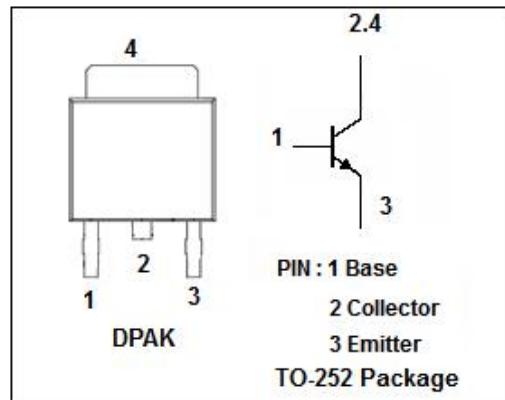
2STD1665

### DESCRIPTION

- Low collector saturation voltage
- High current gain characteristics
- Fast-switching speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

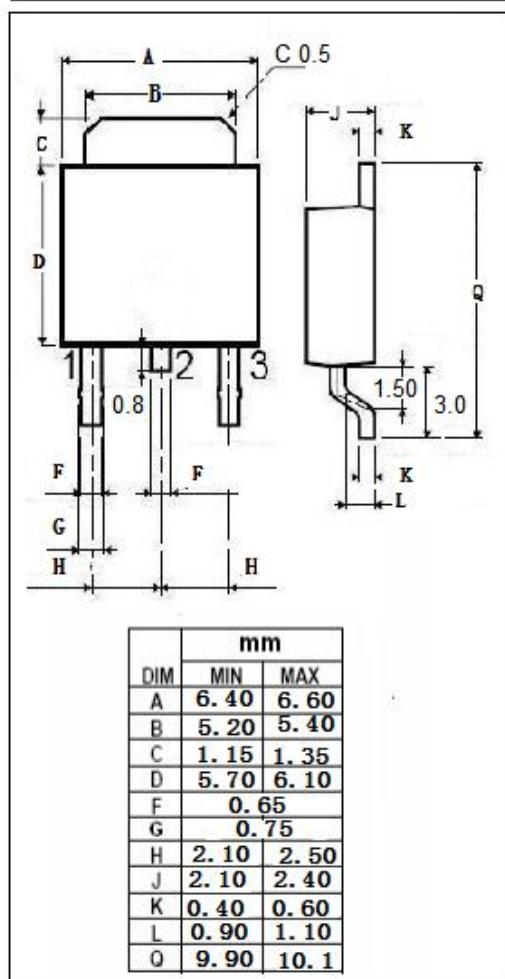
### APPLICATIONS

- Voltage regulators
- High efficiency low voltage switching



### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	65	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_c$	Collector Current-Continuous	6	A
$I_{CM}$	Collector Peak Current	20	A
$P_c$	Collector Power Dissipation	15	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2STD1665****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)-1</sub> <sup>NOTE</sup>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.1A; I <sub>B</sub> = 5mA			50	mV
V <sub>CE(sat)-2</sub> <sup>NOTE</sup>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.0A; I <sub>B</sub> = 50mA			0.12	V
V <sub>CE(sat)-3</sub> <sup>NOTE</sup>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.0A; I <sub>B</sub> = 50mA			0.20	V
V <sub>CE(sat)-4</sub> <sup>NOTE</sup>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6.0A; I <sub>B</sub> = 150mA			0.60	V
V <sub>CE(sat)-5</sub> <sup>NOTE</sup>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 300mA			0.38	V
V <sub>BE(sat)</sub> <sup>NOTE</sup>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 200mA			1.15	V
V <sub>BE(ON)</sub> <sup>NOTE</sup>	Base-Emitter On Voltage	I <sub>C</sub> = 4A; V <sub>CE</sub> =1V			1.0	V
I <sub>CB0</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			50	nA
I <sub>EB0</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			10	nA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 10mA; V <sub>CE</sub> = 1V	150			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 1V	150		350	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 1V	90			
h <sub>FE-4</sub>	DC Current Gain	I <sub>C</sub> = 10A; V <sub>CE</sub> = 1V	30			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		45		pF

NOTE:Pulse test PW≤300us,duty cycle ≤2%

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